Diode Semiconductor Device - Page 1 of 1



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Inclosure Ma	
Glass	
Overall Leng	gth:
0.300 inches	
Terminal Le	ngth:
1.500 inches	
Overall Dian	neter:
0.107 inches	
Joint Electro	onic Device Engineering Council/jedec/case Outline Designation:
Do-7	
Mounting M	ethod:
Terminal	
Features Pro	ovided:
Hermetically	sealed case and quality assurance level txv
Semiconduc	ctor Material:
Silicon	
Voltage Rati	ng In Volts Per Characteristic:
60.0 working	g peak reverse voltage, peak total value
Current Rati	ng Per Characteristic:
10.00 microa	mperes forward current, average peak
Power Ratin	g Per Characteristic:
400.0 watts s	mall-signal input power, common-collector preset
Maximum O	perating Tempurature Per Measurement Point:
175.0 degree	es celsius ambient air
Test Data De	ocument:
81349-mil-s-	19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specificat
format; exclu	Ides commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmenta	al and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Ty	pe And Quantity:
2 uninsulated	l wire lead
Specificatio	n Data:
81349-mil-s-	19500/383 government specification
Shelf Life:	
N/a	
Unit Of Mea	sure:
Demilitariza	tion:
No	
Fiig:	
A110a0	